



STB28NM60ND Information



For Reference Only

Part Number STB28NM60ND
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 23A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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STB28NM60ND Specifications

Manufacturer Part Number STB28NM60ND Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series FDmesh? II FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 23A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 62.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2090pF @ 100V Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Report errors?		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeriesFDmesh? IIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250µAGate Charge (Qg) (Max) @ Vgs62.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2090pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs150 mOhm @ 11.5A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer Part Number	STB28NM60ND
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FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs for Early (Qg) (Max) @ Vds Vgs (Max) Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case N-Channel NOSFET (Metal Oxide) 10V 23A (Tc) 10V 250μA 62.5nC @ 10V 2090pF @ 100V 2090pF @ 10V 2090pF @ 100V 2090pF @ 100V 2090pF @ 100V 2090pF @ 100V 20	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs62.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2090pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs150 mOhm @ 11.5A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	FDmesh? II
Drain to Source Voltage (Vdss)600 VCurrent - Continuous Drain (Id) @ 25°C23A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs62.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2090pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs150 mOhm @ 11.5A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package Package / Case 23A (Tc) 24A (Tc) 5V @ 250µA 62.5nC @ 10V 2090pF @ 100V 2090pF @ 100V 2150V 225V FET Feature - Power Dissipation (Max) 190W (Tc) 150 mOhm @ 11.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs62.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2090pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)190W (Tc)Rds On (Max) @ Id, Vgs150 mOhm @ 11.5A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Input Capacitance (Ciss) (Max) @ Vds 150 mOhm @ 11.5A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	23A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +25V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case 62.5nC @ 10V 2090pF @ 100V 190W (Tc) 150°C TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) EET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	62.5nC @ 10V
FET Feature - Power Dissipation (Max) 190W (Tc) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	2090pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150 mOhm @ 11.5A, 10V Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs150 mOhm @ 11.5A, 10VOperating Temperature150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	190W (Tc)
Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	150 mOhm @ 11.5A, 10V
Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	150°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	D2PAK
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

STB28NM60ND Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STB28NM60ND Payment Methods



















STB28NM60ND Shipping Methods













If you have any question about STB28NM60ND, please do not hesitate to contact us!

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